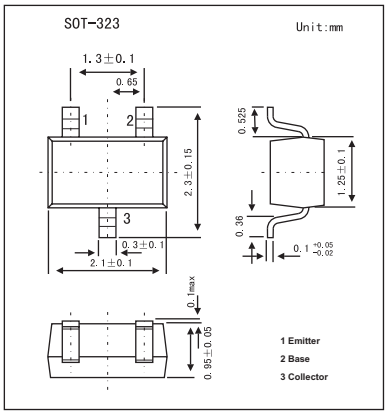
Silicon PNP Epitaxial Planar Type

2SA1531A



Features

- Low noise voltage NV.
- High forward current transfer ratio hFE.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-55	V
Collector-emitter voltage	V_{CEO}	-55	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-50	mA
Peak collector current	I_{CP}	-100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	I_C = -10 μA, I_E = 0	-55			V
Collector-emitter voltage	V_{CEO}	I_C = -2 mA, I_B = 0	-55			V
Emitter-base voltage	V_{EBO}	I_E = -10 μA, I_C = 0	-5			V
Base-emitter voltage	V_{BE}	V_{CE} = -1 V, I_C = -100 mA		-0.7	-1	V
Collector-base cutoff current	I_{CBO}	V_{CB} = -10 V, I_E = 0			-0.1	μA
Collector-emitter cutoff current	I_{CEO}	V_{CE} = -10 V, I_B = 0			-1	μA
Forward current transfer ratio	hFE	V_{CE} = -5 V, I_C = -2 mA	180		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -100 mA, I_B = -10 mA			-0.6	V
Transition frequency	f_T	V_{CB} = -5 V, I_E = 2 mA, f = 200 MHz		150		MHz
Noise voltage	C_{ob}	V_{CE} = -10 V, I_C = -1 mA, G_V = 80 dB, R_g = 100 k? , Function = FLAT			150	mV

hFE Classification

Marking	H		
Rank	R	S	T
hFE	180～360	260～520	360～700